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Front Matter: Volume 9818

, "Front Matter: Volume 9818," Proc. SPIE 9818, 2016 International Workshop on Information Data Storage and Tenth International Symposium on Optical Storage, 981816 (18 November 2016); doi: 10.1117/12.2264274

SPIE.

Event: 2016 International Workshop on Information Data Storage and Tenth International Symposium on Optical Storage, 2016, Changzhou, China

PROCEEDINGS OF SPIE

2016 International Workshop on Information Data Storage and Tenth International Symposium on Optical Storage

**Fuxi Gan
Zhitang Song**
Editors

**10–13 April 2016
Changzhou, China**

Organized and Sponsored by

Shanghai Institute of Microsystem and Information Technology, CAS (China)
Shanghai Institute of Optics and Fine Mechanics, CAS (China)
Jiangsu University of Technology (China)

Co-sponsored by

National Natural Science Foundation of China (China)
Chinese Academy of Sciences (China)
Science and Technology Commission of Shanghai Municipality (China)

Published by
SPIE

Volume 9818

Proceedings of SPIE 0277-786X, V. 9818

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

2016 International Workshop on Information Data Storage and Tenth International Symposium
on Optical Storage edited by Fuxi Gan, Zhitang Song, Proc. of SPIE Vol. 9818, 981816
© 2016 SPIE CCC code: 0277-786X/16/\$18 · doi: 10.1117/12.2264274

Proc. of SPIE Vol. 9818 981816-1

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Author(s), "Title of Paper," in *2016 International Workshop on Information Data Storage and Tenth International Symposium on Optical Storage*, edited by Fuxi Gan, Zhitang Song, Proceedings of SPIE Vol. 9818 (SPIE, Bellingham, WA, 2016) Six-Digit Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510600591

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) • Fax +1 360 647 1445

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Introduction

The 2016 International Workshop on Information Storage/Tenth International Symposium on Optical Storage (IWIS/ISOS 2016) was held 10–13 April 2016 in Changzhou City, Jiangsu Province, China, under the auspices of the National Natural Science Foundation of China, Chinese Academy of Sciences (CAS), and Science and Technology Commission of Shanghai Municipality. The workshop/symposium was organized by Shanghai Institute of Microsystem and Information Technology (SIMIT), CAS, Shanghai Institute of Optics and Fine Mechanics (SIOM), CAS and Jiangsu University of Technology. More than 100 scientists, technologists, and experts from universities, research institutes, and industries of 8 countries and regions participated in the workshop/symposium, which provided a forum for reviewing recent progress and exchanging information in a wide range of topics including materials, physics, devices, measurement and manufacturing technologies in information storage. 92 papers were presented at the workshop/symposium, including 35 as oral presentations and 57 as posters.

As predecessors of this workshop/symposium, the previous nine symposia of the ISOS series were successfully held in Shanghai 1988, Chongqing 1990, Kunming 1992, Shenzhen 1996, Shanghai 2000, Wuhan 2002, Zhanjiang 2005, Wuhan 2008 and Shanghai 2012, respectively. From the 8th symposium, the ISOS meeting extended its topics, and a workshop on information storage was added due to the merging of data storage technologies in recent years. The workshop/symposium promoted discussions on both the theoretical aspects and practical applications of information storage and strengthened cooperation and friendship in the semiconductor, optical and magnetic memory communities.

We are very grateful to the members of the International Advisory Committee, the Local Organizing and Technical Committee, as well as the Secretariat for their fruitful work in the preparation and operation of the workshop/symposium. Thanks are also extended to our invited speakers and all of the contributing authors for their elaborate preparation of the presentations or manuscripts. Finally, we gratefully acknowledge the sponsors and cosponsors, without whose support we could not have held such a successful workshop/symposium.

Fuxi Gan
Zhitang Song